

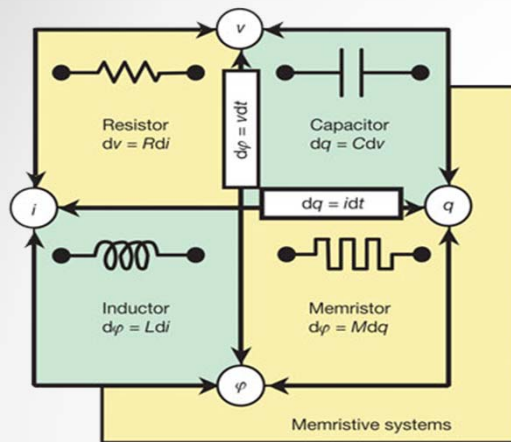
Analog circuits implementation using coherer based memristor

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Contents

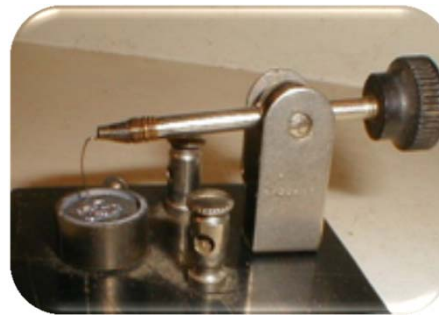
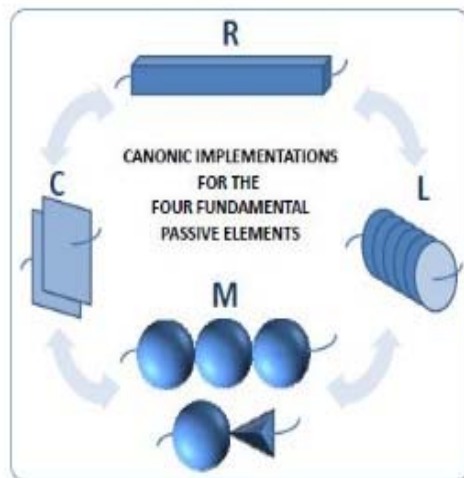
- Canonical Implementation of memristive system
- Characterization setup
- Experimental observations
- Programmable Analog circuits
- Conclusion

Memristive system discovery

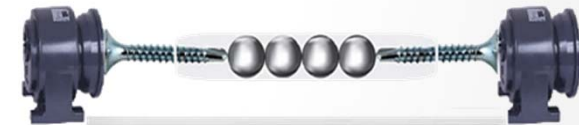


- Memristive system realized in 2008 and different forms of system exists-
1. ReRam
 2. Spintronic Memristors
 3. Phase change memory
 4. CBRAM

- The canonical implementation of memristive system was recently published by the group.



Metal-semiconductor point contact



Metal-metal point contact

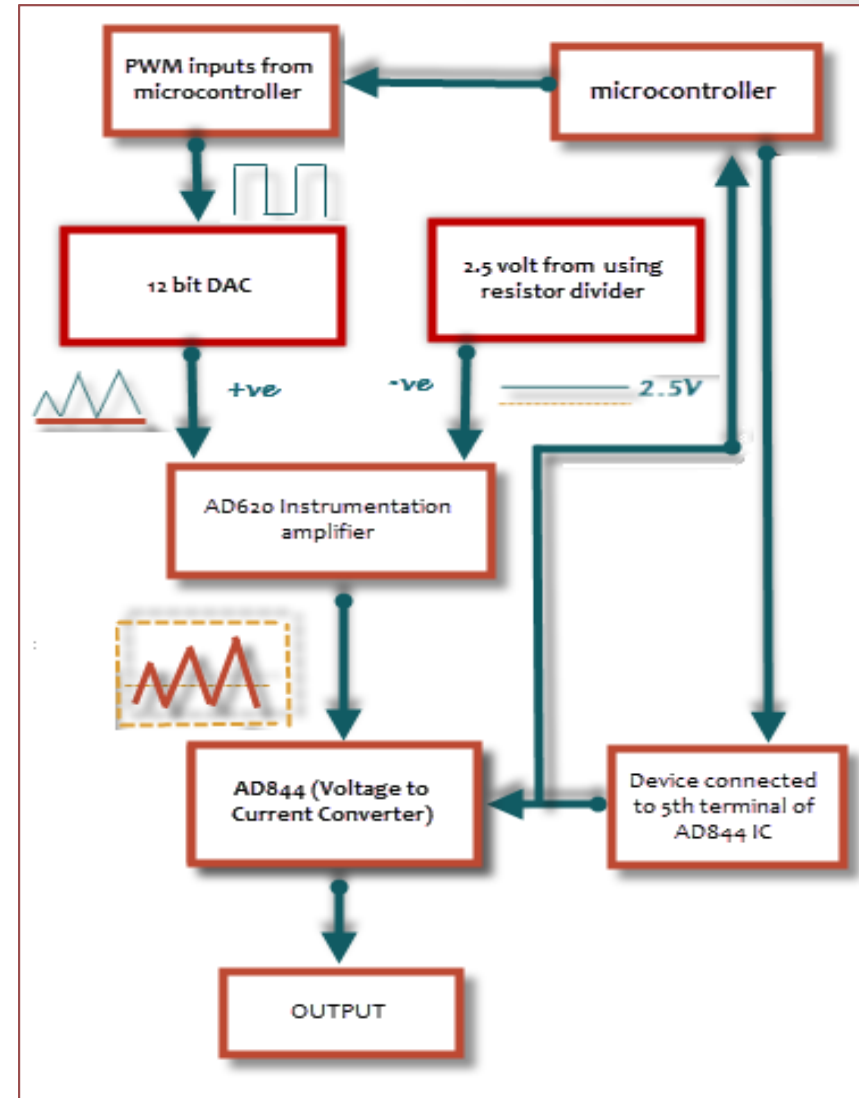
- 1- *The first radios were made using memristors!* . G. Gandhi, V. Aggarwal, and L. Chua. *Circuits and Systems Magazine*.
- 2- L.O. Chua, "Memristor – The Missing Circuit Element," *IEEE Trans.*, 1971

Characterization setup

- Device was found to be current controlled, hence we input current peaks and observe the output voltage across the device to obtain the required I-V curves.

The main components installed in the current board include-

- AD844 (current feedback operational amplifiers).
- MCP4725 (12-Bit I²C Digital to Analog Converter)
- AD620 (Instrumentation Amplifier IC).



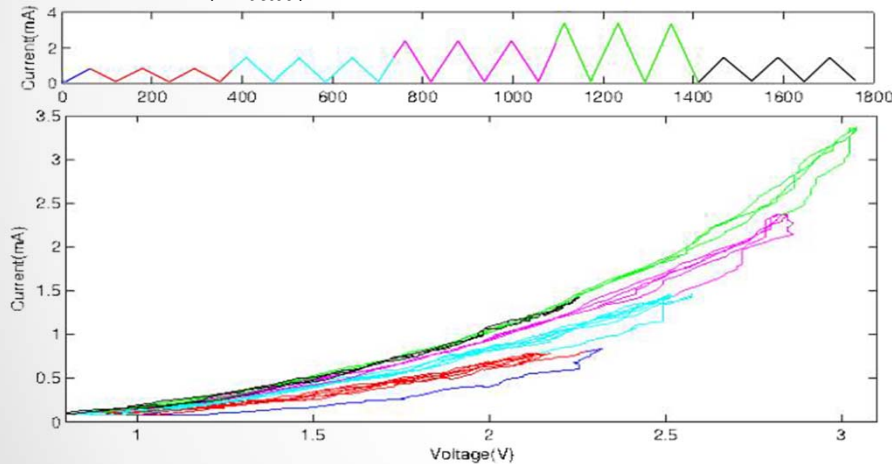
Flow Chart

Characteristics

- We have observed that coherer setup exhibits-

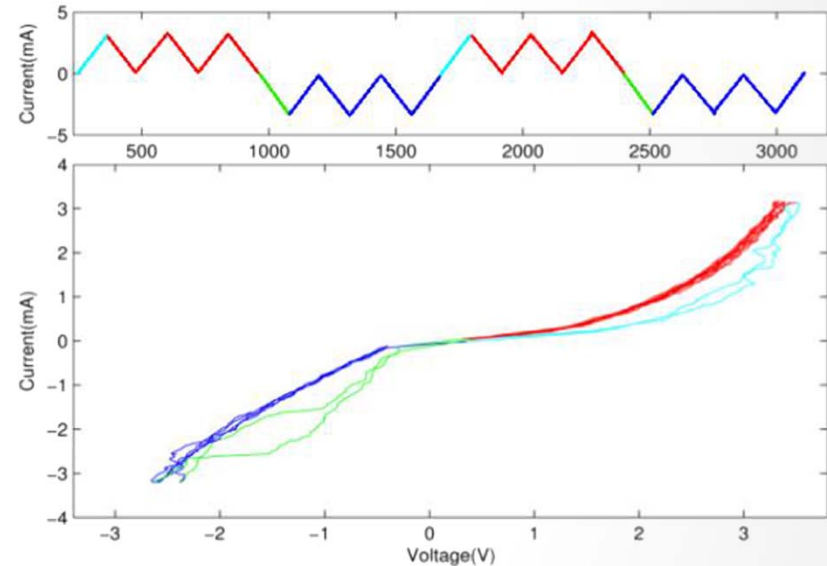
Maximum Current Resistance

Behaviour(I_{max}): The resistance changes as the maximum current passing through the device changes. This demonstrates that the device at contact level has some kind of memory which makes it remember the amount of current that has passed through it. $R=f(I_{max})$



- Non-linearity, resistance range, threshold voltage is found to be dependent on the area, location and pressure applied.

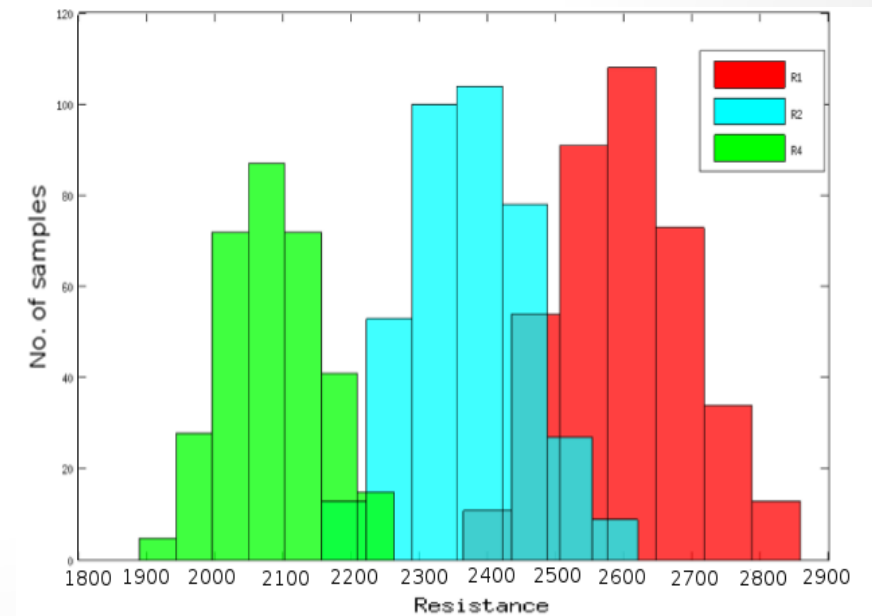
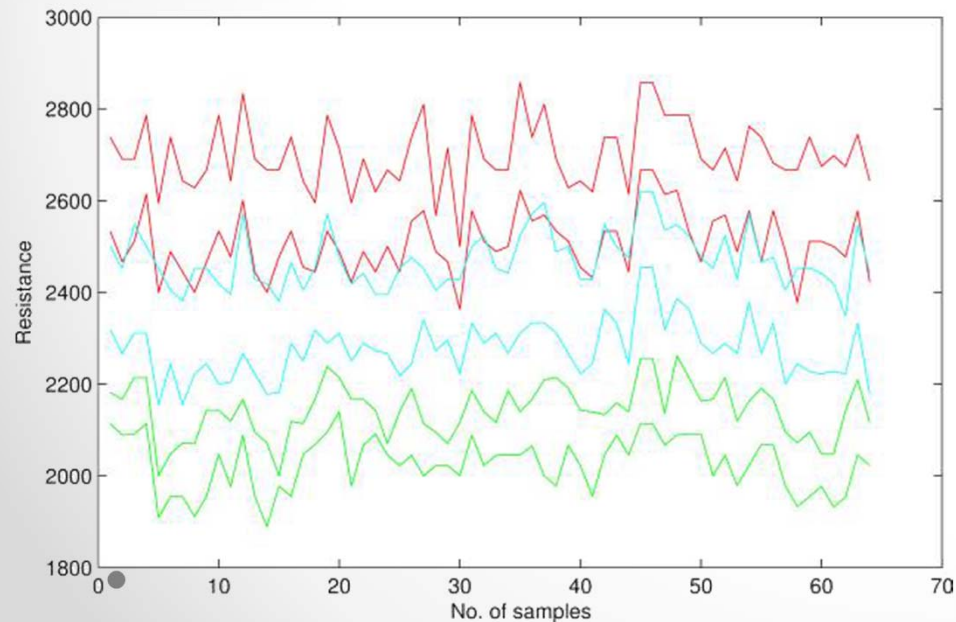
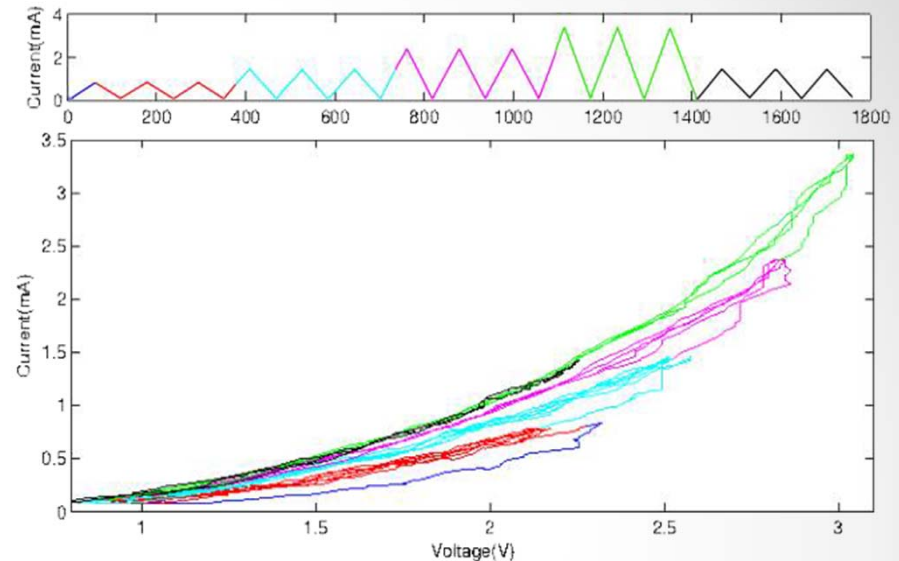
Bistable Memristive Behaviour: We have demonstrated that under suitable bipolar input, the device exhibits pinched hysteresis.



- The device gets programmed in each direction by a large positive/negative input peak current and remains in the same resistance state when provided with a smaller input current.

Experimental observations

- The DC resistance at 0.7mA is plotted for various samples. Minimum and Maximum resistance in each sample is plotted.
- Device can be programmed in three different resistance ranges.
- Larger the difference between the currents, more the two dc resistance range separated.



Applications build using memristor and board

- Device can be programmed by high amplitude current pulses and low amplitude current pulses can be used in analog operation.
- Each programming current pulse changes the resistance by a discrete amount.

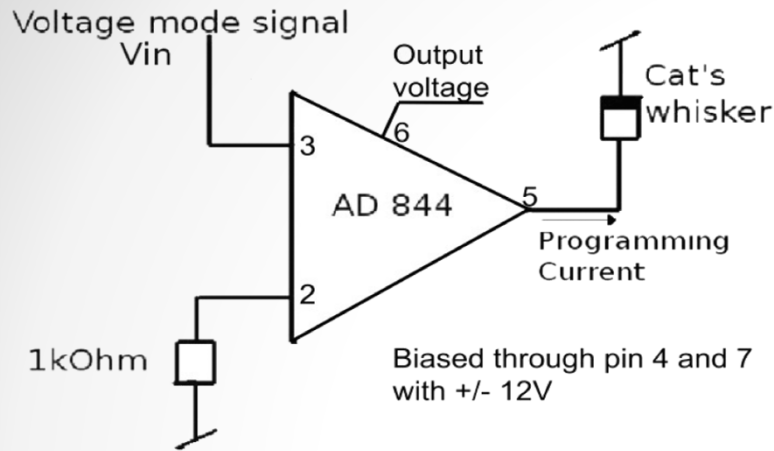
Programmable analog circuits

Programmable gain
amplifier

Programmable
threshold comparator

Programmable
switching thresholds
Schmitt trigger

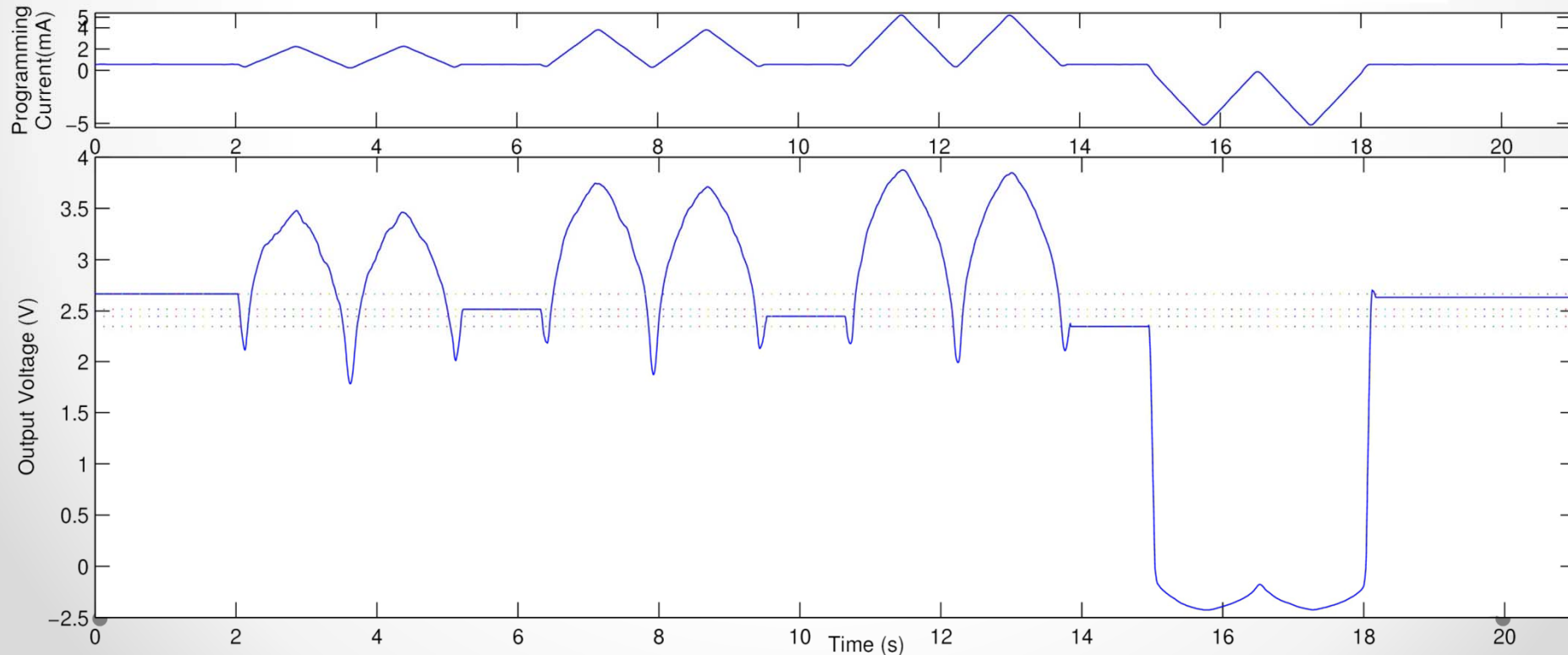
a) Programmable Gain Amplifier



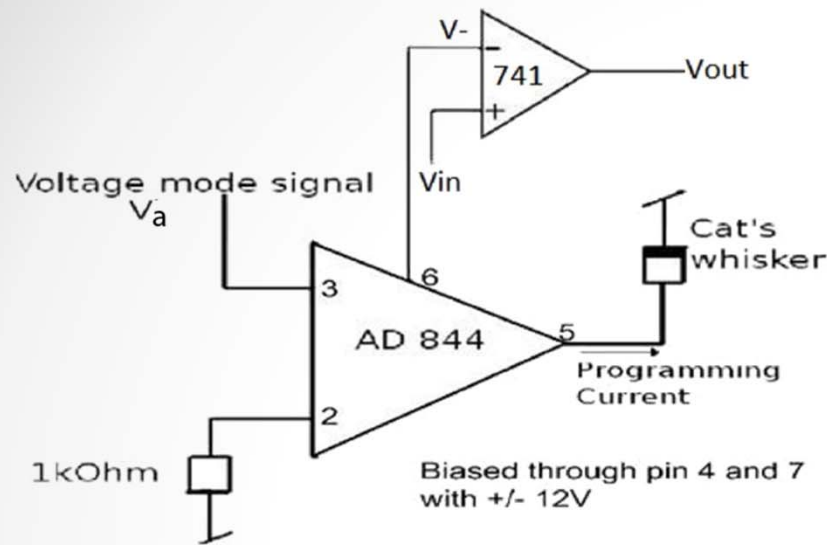
- Programming current $I = V_{in}/R$;
- Output Voltage $V_{out} = I * M(r)$;
- $R = 1k\Omega$;
- $V_{out}/V_{in} = M(r)/R$;

Amplifier gain is controlled by triangle pulses.

Gain decreases with every rising pulse and changes by 11.7% with peak of 5mA current.



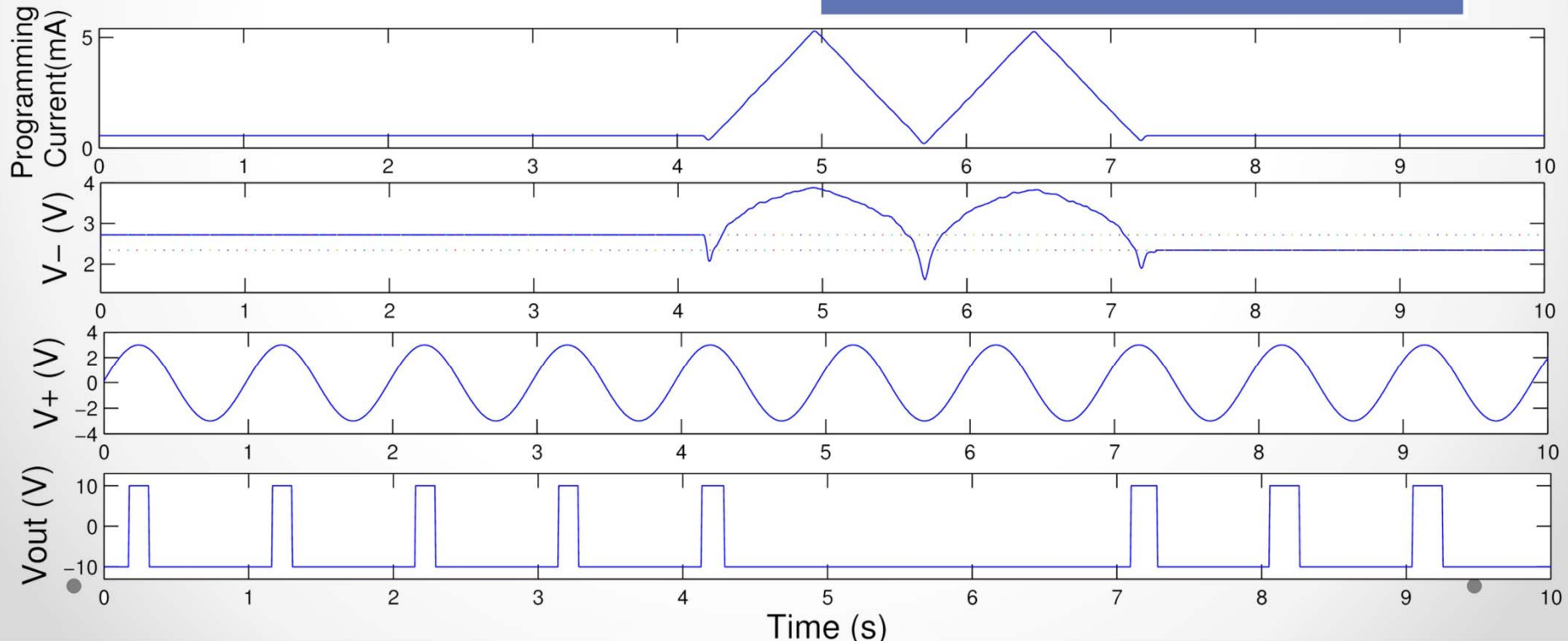
b) Programmable threshold comparator



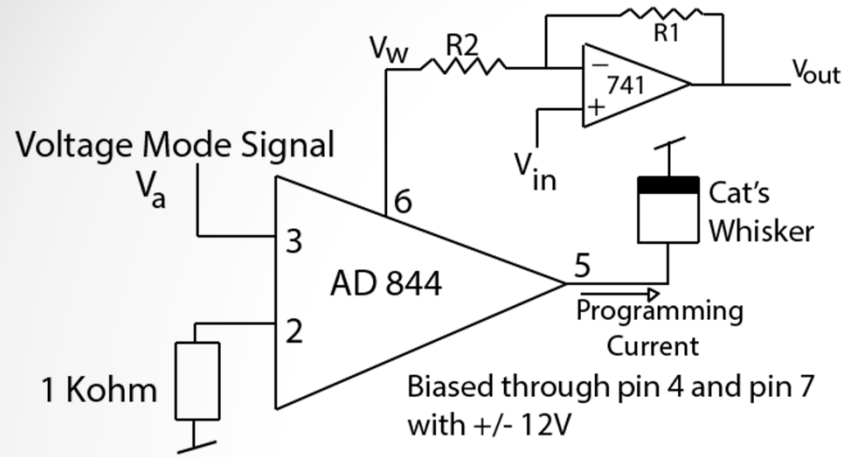
- $V_- = V_a \frac{M(r)}{R}$
- V_a is the voltage mode signal input.
- $V_{in} = 3\sin(2\pi ft)$ where $f = 1\text{Hz}$.

Threshold V_- controlled by programming current.

At 5mA current, resistance changes by 670ohms, hence wider output from $t=7\text{sec}$.



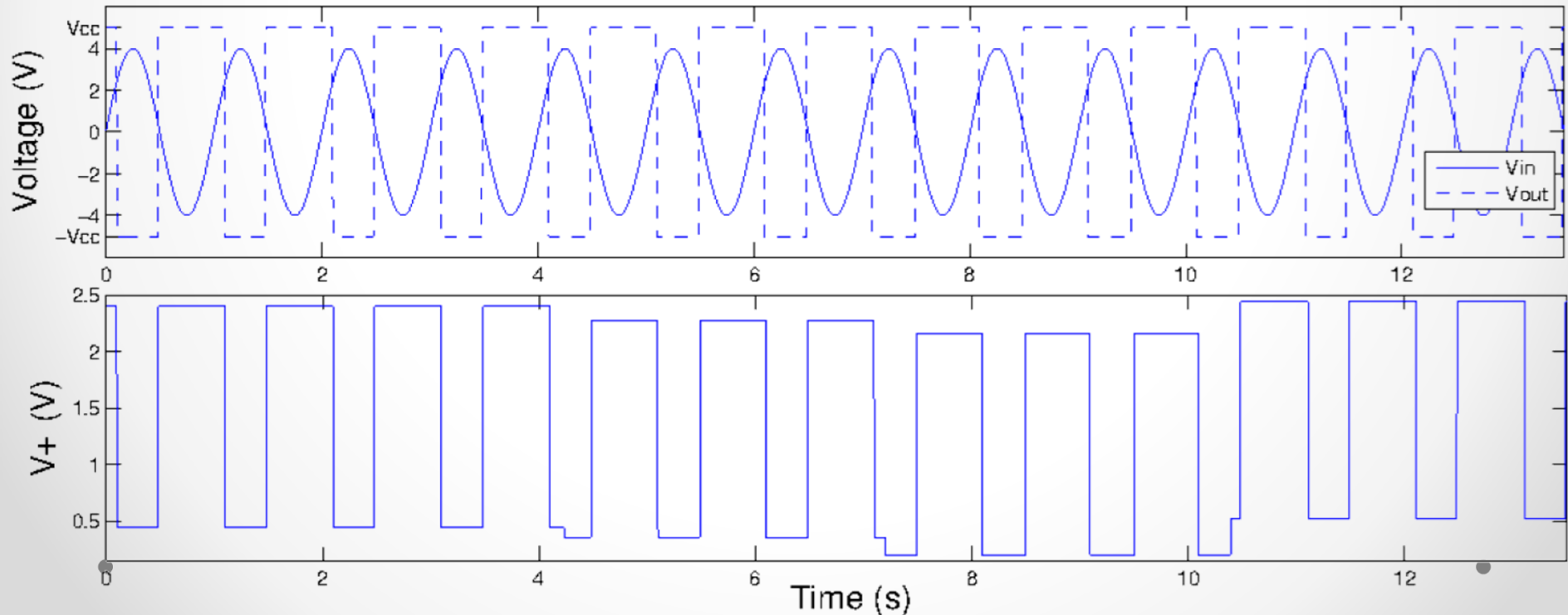
c) Programmable switching threshold schmitt trigger.



- Two switching threshold given by $\left(\frac{\pm V_{cc}R_2 + V_w R_1}{R_1 + R_2}\right)$
- $V_{cc} = 10V$; $R_1 = 10k\Omega$; $R_2 = 100\Omega$
- $V_{in} = 4\sin(2\pi ft)$ where $f = 1Hz$.

Voltage V_w controlled using programming pulses.

Threshold changes hence output voltage V_{out} occurs at different values of V_{in} .



Conclusion

- We have discussed about the canonical implementation of memristive system.
- We have designed applications using this memristor which shows that coherer based memristor is as reliable as other memristors.
- Provides community with inexpensive memristor which can be implemented by anyone.

Future work!

- Building a reliable electrical model for the device.
- Studying the dynamics of resistive grid architecture based on the presented memristor.

Thanks!

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